

# SCHOTTKY BARRIER DIODE

## Features

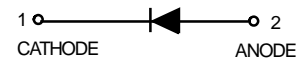
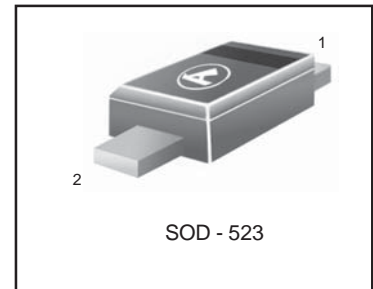
- (1) Small surface mounting type SC-79/SOD523
- (2) Low reverse current and low forward voltage.
- (3) High reliability

## Construction

silicon epitaxial planar

We declare that the material of product compliance with RoHS requirements.

**LRB751S-40T1G**



## MAXIMUM RATINGS (T<sub>A</sub> = 25°C)

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V <sub>RM</sub>	40	V
DC reverse voltage	V <sub>R</sub>	30	V
Mean rectifying current	I <sub>O</sub>	30	mA
Peak forward surge current	I <sub>FSM</sub>	200	mA
Junction temperature	T <sub>j</sub>	125	°C
Storage temperature	T <sub>stg</sub>	-40~+125	°C

## DEVICE MARKING

LRB751S-40T1G= 5

## ELECTRICAL CHARACTERISTICS(T<sub>A</sub> = 25°C)

Parameter	Symbol	Min.	Typ	Max.	Unit	Conditions
Forward voltage	V <sub>F</sub>	-	-	0.37	V	I <sub>F</sub> =1mA
Reverse current	I <sub>R</sub>	-	-	0.5	μA	V <sub>R</sub> =30V
Capacitance between terminals	C <sub>T</sub>	-	2.0	-	pF	V <sub>R</sub> =1V, f=1MHz

## Ordering Information

Device	Marking	Shipping
LRB751S-40T1G	5	3000/Tape&Reel
LRB751S-40T3G	5	10000/Tape&Reel

LRB751S-40T1G

Electrical characteristic curves( $T_A = 25^\circ\text{C}$ )

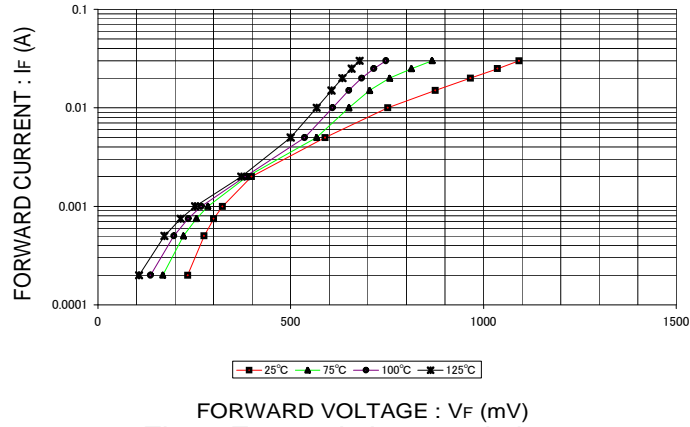


Fig. 1 Forward characteristics

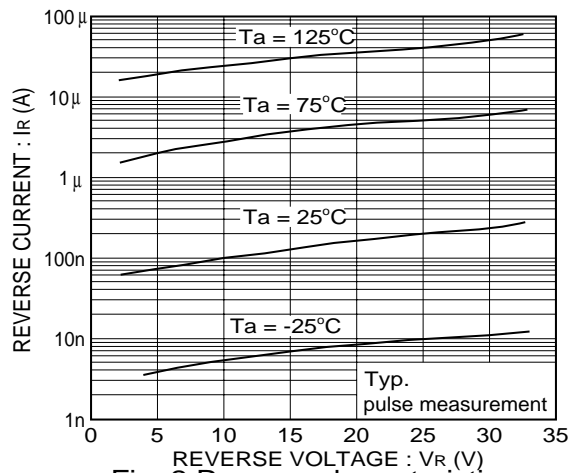


Fig. 2 Reverse characteristics

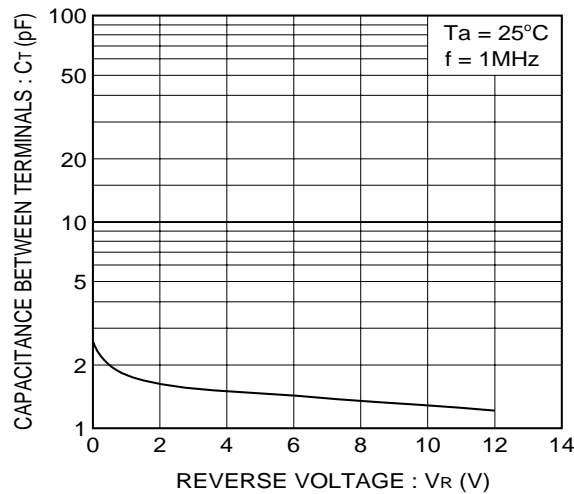
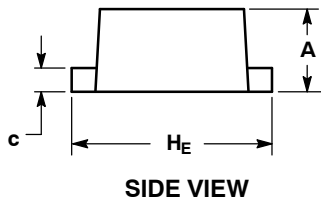
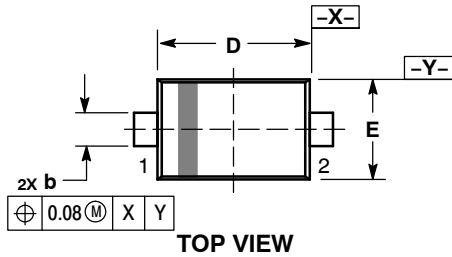


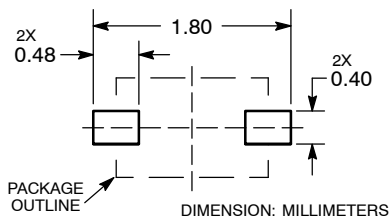
Fig. 3 Capacitance between terminals characteristics

LRB751S-40T1G

SC-79/SOD-523



**RECOMMENDED  
SOLDERING FOOTPRINT\***



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	0.50	0.60	0.70
b	0.25	0.30	0.35
c	0.07	0.14	0.20
D	1.10	1.20	1.30
E	0.70	0.80	0.90
H <sub>E</sub>	1.50	1.60	1.70
L	0.30 REF		
L2	0.15	0.20	0.25